

new**TD•0062**

Low power dual BI-FET operational amplifiers.



SO 8



DIL 8

The TD•0062, are high speed dual J-FET input operational amplifiers. Each of these incorporates well matched, high voltage J-FET and bipolar transistors in a monolithic integrated circuit.

The devices feature high slew rate, low input bias and offset currents, and low offset voltage temperature coefficient.

- Very low power consumption.
- Wide common-mode and differential voltage ranges.
- Low input bias and offset currents.
- Typical supply current 200 μ A.
- Output short-circuit protection.
- High impedance J-FET input stage.
- Internal frequency compensation.
- Latch-up free operation.
- High slew rate 3.5 V/ μ s typ.

BI-FET OPERATIONAL AMPLIFIERS

CHARACTERISTIC	SYMBOL	UNIT	SINGLE						DUAL						QUAD					
			± 18																	
Supply voltage	V_{CC} max.	V	± 18																	
Input offset voltage	V_{IO} max.	mV	10	15	10	10	10	10	15	10	15	10	15	10	15	10	15	10		
Input offset current	I_{IO} max.	nA	0.05	0.2	0.05	0.05	0.05	0.05	0.1	0.2	0.05	0.2	0.1	0.2	0.05	0.2	0.1	0.2		
Input impedance	Z_I typ.	$10^8 M\Omega$	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1		
Input bias current	I_B max	nA	0.2	0.4	0.2	0.2	0.2	0.2	0.4	0.2	0.4	0.2	0.4	0.2	0.2	0.4	0.2	0.2		
Slew rate	S_v typ.	$V/\mu s$	13	13	5	12	50	13	3.5	13	13	13	3.5	13	13	13	13	13		
Supply voltage rejection ratio	S_vR min.	dB	70	70	80	80	80	70	70	70	70	70	70	70	70	70	70	70		
Gain x bandwidth	B typ.	MHz	3	3	2.5	4.5	20	4	1	3	3	4	1	3	3	4	1	3		
Voltage gain	A_v min.	V/mV	25	25	25	25	25	25	3	25	25	25	3	25	25	25	25	25		
Input voltage range	(V_I max.) min.	V	± 11	± 10	± 10	± 10	± 10	± 11												

TD•0071 TD•0081 TD•0155 TD•0156 TD•0157 TD•0351 TD•0062 TD•0072 TD•0082 TD•0353 TD•0064 TD•0074 TD•0084 TD•0347

	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	Plastic SO 8-14
	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	Plastic DIL 8-14
	●	●	●	●	●	●	●	●	●	●	●	●	●	●	●	●	●	Cerdip DIL 14
	●	●	●	●	●	●	●	●	●	●	●	●	●	●	●	●	●	Chip carrier
	●	●	●	●	●	●	●	●	●	●	●	●	●	●	●	●	●	Metal can TO 99